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# Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









rfmd.com

## **Preliminary**

# **SGA-0363(Z)**

# DC to 5000 MHz, SILICON GERMANIUM CASCADABLE GAIN BLOCK

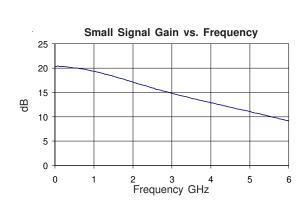
APP.

RFMD Green, RoHS Compliant, Pb-Free (Z Part Number)
Package: SOT-363

#### **Product Description**

The SGA-0363 is a high performance SiGe HBT MMIC Amplifier. A Darlington configuration featuring one-micron emitters provides high FT and excellent thermal perfomance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only two DC-blocking capacitors, a bias resistor and an optional RF choke are required for operation.





#### **Features**

- DC to 5000MHz Operation
- Single Voltage Supply
- Low Current Draw: 11mA at 2.5 V Typ.
- High Output Intercept: 14dBm Typ. at 1950MHz

#### **Applications**

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite

Parameter	Specification		Unit	O and it is a	
raiailletei	Min.	Тур.	Max.	UIIIL	Condition
Output Power at 1dB Compression		2.3		dBm	850MHz
		2.3		dBm	1950MHz
		1.6		dBm	2400 MHz
Third Order Intercept Point		14.2		dBm	850MHz
		14.0		dBm	1950MHz
		13.1		dBm	2400MHz
Small Signal Gain		19.6		dB	850MHz
		17.2		dB	1950MHz
		16.2		dB	2400MHz
3dB Bandwidth		5000		MHz	
Input VSWR		1.8:1			DC to 4500 MHz
Output VSWR		1.7:1			DC to 4500MHz
Reverse Isolation		24.0		dB	850MHz
		22.8		dB	1950MHz
		22.1		dB	2400 MHz
Noise Figure <sup>[1]</sup>		3.0		dB	1950MHz
Device Operating Voltage		2.5		V	
Device Operating Current	9	11	13	mA	
Thermal Resistance		255		°C/W	junction - lead

 $\textbf{Test Conditions: V}_S = \textbf{5V}, \textbf{I}_D = \textbf{11} \textbf{mA Typ., T}_L = 25 \text{ °C. OIP3 Tone Spacing} = \textbf{1MHz}, \textbf{P}_{OUT} \text{ per tone} = -\textbf{12} \text{ dBm}, \textbf{R}_{BIAS} = 220 \Omega, \textbf{Z}_S = \textbf{Z}_L = 50 \Omega$ 

### **Preliminary**



#### **Absolute Maximum Ratings**

Parameter	Rating	Unit
Device Current (I <sub>D</sub> )	22	mA
Device Voltage (V <sub>D</sub> )	6	V
RF Input Power	-5	dBm
Junction Temp (T <sub>J</sub> )	+150	°C
Operating Temp Range (T <sub>L</sub> )	-40 to +85	°C
Storage Temp	+150	°C

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one. Bias Conditions should also satisfy the following expression:  $I_DV_D\!<\!(T_J\!-\!T_L)/R_{TH},j\!-\!I$ 



#### Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

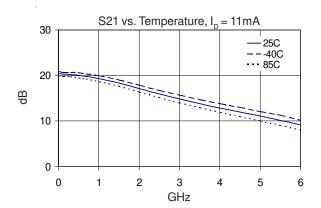
RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

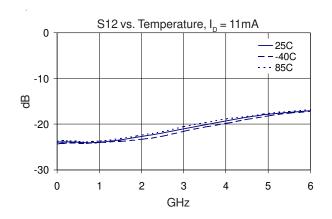
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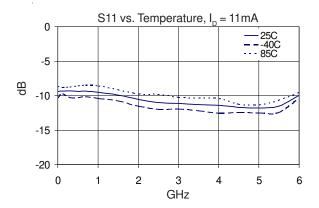
Dawanastan		Specification		Unit	Oandikian	
Parameter	Min.	Тур.	Max.	Unit	Condition	
Gain		20.4		dB	100 MHz	
		20.0		dB	500MHz	
		19.6		dB	850MHz	
		17.2		dB	1950MHz	
		16.2		dB	2400MHz	
		13.8		dB	3500MHz	
Output IP <sub>3</sub>		14.8		dBm	100 MHz, Tone spacing=1MHz, P <sub>OUT</sub> per tone= -12 dBm	
		14.5		dBm	500 MHz, Tone spacing=1MHz, P <sub>OUT</sub> per tone= -12dBm	
		14.2		dBm	850 MHz, Tone spacing=1MHz, P <sub>OUT</sub> per tone= -12dBm	
		14.0		dBm	1950MHz, Tone spacing=1MHz, P <sub>OUT</sub> per tone= -12dBm	
		13.1		dBm	2400MHz, Tone spacing=1MHz, P <sub>OUT</sub> per tone= -12dBm	
		11.5		dBm	3500 MHz, Tone spacing=1MHz, P <sub>OUT</sub> per tone= -12dBm	
Output P1dB		3.2		dBm	100 MHz	
		2.9		dBm	500MHz	
		2.3		dBm	850MHz	
		2.3		dBm	1950MHz	
		1.6		dBm	2400MHz	
		0.8		dBm	3500MHz	
Input Return Loss		9.3		dB	100 MHz	
		9.4		dB	500MHz	
		9.4		dB	850MHz	
		10.4		dB	1950MHz	
		10.8		dB	2400MHz	
		11.3		dB	3500MHz	
Reverse Isolation		23.9		dB	100MHz	
		23.9		dB	500MHz	
		24.0		dB	850MHz	
		22.8		dB	1950MHz	
		22.1		dB	2400MHz	
		20.1		dB	3500 MHz	
Noise Figure		2.9		dB	100 MHz, $Z_S$ =50 Ω	
		2.8		dB	500MHz, Z <sub>S</sub> =50Ω	
		3.0		dB	850MHz, $Z_S = 50\Omega$	
		3.0		dB	1950MHz, $Z_S = 50\Omega$	

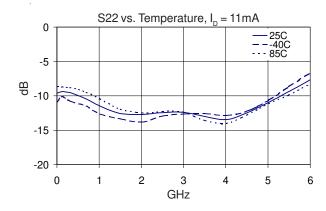
Test Conditions: I<sub>D</sub>=8mA, unless otherwise noted

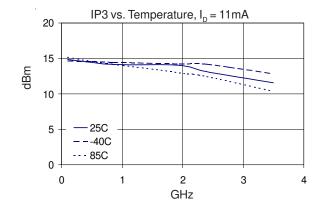
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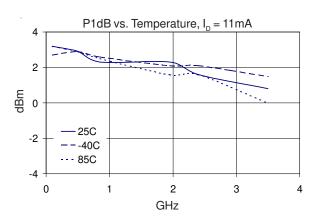










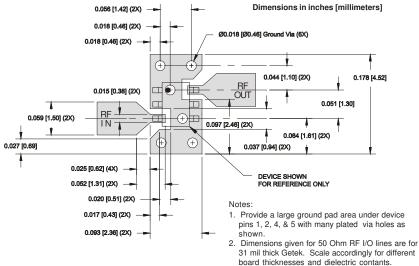




Function	Description
RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.
GND	Connection to ground. Use via holes for best performance to reduce lead inductance as close to ground leads as possible.

#### Pin 3 1, 2, 4, 5 **RF OUT/BIAS** RF output and bias pin. DC voltage is present on this pin, therefore a DC blocking capacitor is necessary for proper oper-6

### **Suggested Pad Layout**



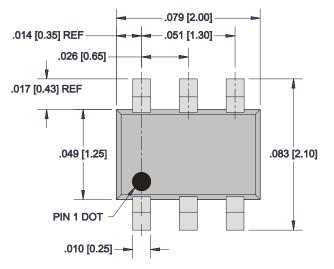
board thicknesses and dielectric contants.

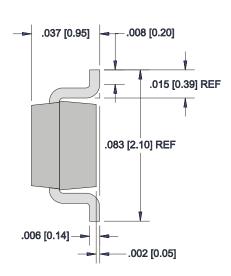
3. We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31 mil thick Getek with 1 ounce copper on both sides.

### **Package Drawing**

Dimensions in inches (millimeters)

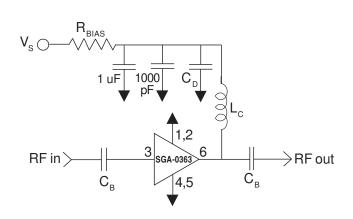
Refer to drawing posted at www.rfmd.com for tolerances.







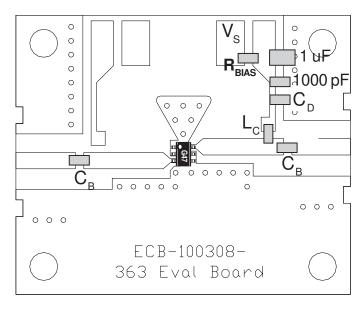
### **Application Schematic**



Reference	Frequency (Mhz)					
Designator	500	850	1950	2400	3500	
C <sub>B</sub>	220 pF	100 pF	68 pF	56 pF	39 pF	
C <sub>D</sub>	100 pF	68 pF	22 pF	22 pF	15 pF	
L <sub>c</sub>	68 nH	33 nH	22 nH	18 nH	15 nH	

Recommended Bias Resistor Values for $I_D$ =11mA $R_{BIAS}$ =( $V_S$ - $V_D$ ) / $I_D$					
Supply Voltage(V <sub>S</sub> )	5 V	7.5 V	9 V	12 V	
$R_{BIAS}$ 220 Ω 470 Ω 620 Ω 910 Ω					
Note: R <sub>plas</sub> provides DC bias stability over temperature.					

## **Evaluation Board Layout**



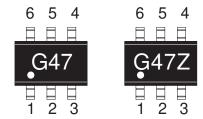
#### **Mounting Instructions**

- 1. Use a large ground pad area near device pins 1, 2, 4, and 5 with many plated through-holes as shown.
- 2. We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31 mil thick FR-4 board with 1 ounce copper on both sides.

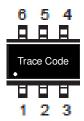
# Preliminary



### **Part Identification Marking**



### **Alternate Marking with Trace Code Only**



### **Ordering Information**

Part Number	Reel Size	Devices/Reel
SGA-0363	7''	3000
SGA-0363Z	7"	3000